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- as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii)) for the following designations AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW, ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG)
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(54) Title: METHOD OF REMOVING IMPURITIES FROM METALLURGICAL GRADE SILICON TO PRODUCE SOLAR GRADE SILICON

(57) Abstract: Metallurgical grade silicon is purified by removing metallic impurities and non-metallic impurities. The object is to produce a silicon species that is suitable for use as solar grade silicon. The process involves grinding metallurgical grade silicon containing metallic and non-metallic impurities to a silicon powder consisting of particles of silicon having a diameter of less than about 5 millimeter. While maintaining the ground silicon powder in the solid state, the ground silicon powder is heated to a temperature less than the melting point of silicon (1410 °C) under reduced pressure. The heated ground silicon powder is maintained at that temperature for a period of time sufficient to enable at least one metallic or non-metallic impurity to be removed from the metallurgical grade silicon.

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